



QUASI-RESONANT PWM SWITCHER

Description

The AP39303 is a highly integrated power switcher with a built-in Quasi-Resonant (QR) PWM controller and a 700V high performance power MOSFET. AP39303 is specially designed for offline power supply that requires ultra-low standby power, high-power density and comprehensive protection. Coordinating with secondary side USBPD or quick charger controller to provide a Flyback charger solution.

At no load or light load, the IC will enter the burst mode to minimize standby power consumption. The minimum switching frequency (typical: 24kHz) is set to avoid the audible noise. When the load increases, the IC will enter QR mode with frequency foldback to improve system efficiency and EMI performance. The maximum switching frequency (typical: 120kHz) is set to clamp the QR frequency to reduce switching power loss. Furthermore, the frequency dithering function is built in to reduce EMI emission.

The AP39303 provides an inner high-voltage start-up function through HV pin which can reduce the standby loss. Moreover, The AP39303 integrates a VCC LDO circuitry, allowing the LDO to regulate the wide range V_{CC_IN} to an acceptable value. This makes the AP39303 to be a good choice in wide range output voltage application.

Internal piecewise linear line compensation ensures constant output power limit over entire universal line voltage range.

Comprehensive protection features are included, such as brown out protection, cycle-by-cycle current limit, VCC Over Voltage Protection (VOVP), Secondary-side Output OVP (SOVP) and UVP (SUVP), internal OTP, Over Load Protection (OLP) and pins' fault protection.

Combined with Diodes Incorporated's synchronous controller APR347, AP39303 system can achieve the higher power conversion efficiency and the better thermal performance.

Features

- Quasi-Resonant Operation under all Line and Load Condition
- Peak Current Mode Control @ DCM
- High-Voltage Startup
- Built-In 700V High Performance Power MOSFET
- Embedded VCC LDO to Guarantee Wide Range V_{CC_IN} Voltage
- Low VCC Charge Current Reduces Standby Power in Output Short Situation
- Adaptive Burst Mode Operation with Output Voltage
- Adaptive Output Power Limit with Output Voltage
- Non-Audible-Noise Quasi-Resonant Control
- Soft Start during Startup Process
- Frequency Fold Back for High Average Efficiency
- Secondary Winding Short Protection with FOCP
- Frequency Dithering for Reducing EMI
- Vcc Maintain Mode
- Useful Pin Fault Protection:

SENSE Pin Floating

FB/Opto-Coupler Open/Short

Comprehensive System Protection Feature:

Programmable External OTP

Over Load Protection (OLP)

Brown In/Out Protection

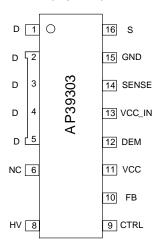
Secondary Side OVP (SOVP) and UVP (SUVP)

- HSOP-16 (Type SM) Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Pin Assignments

(Top View)



HSOP-16 (Type SM)

Applications

- Switching AC-DC Adapter/Charger
- ATX/BTX Auxiliary Power
- Set-Top Box (STB) Power Supply
- Open Frame Switching Power Supply

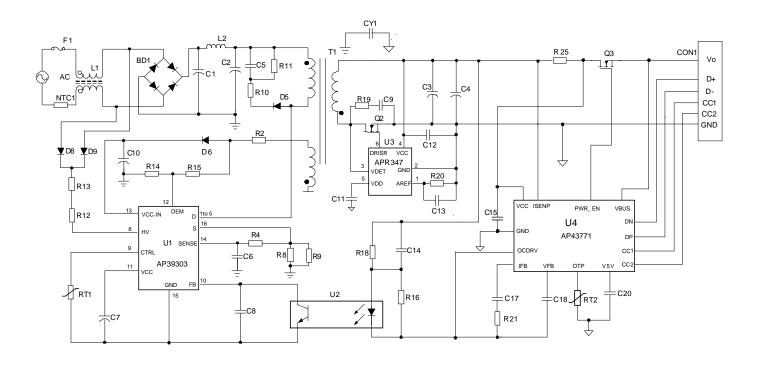
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

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Typical Applications Circuit

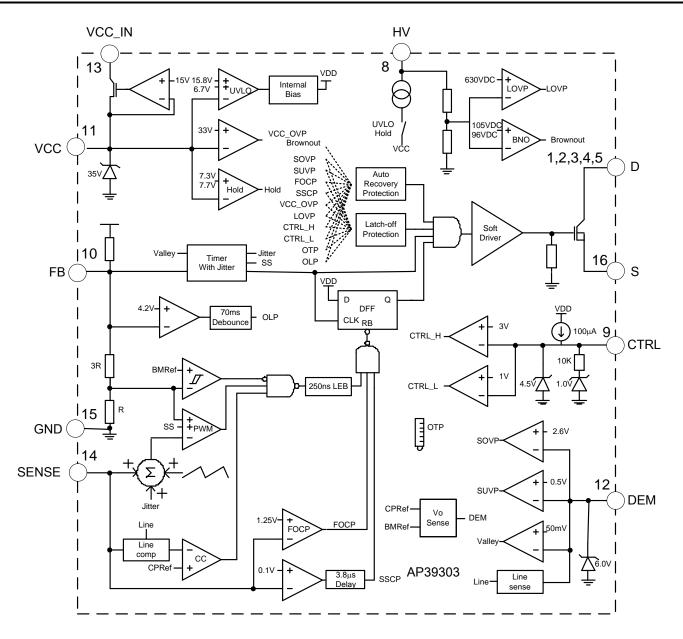


Pin Descriptions

Pin Number	Pin Name	Function
1 to 5	D	The Drain of Internal Power MOSFET
6	NC	Suspended
8	HV	High Voltage Input. Sense Line Voltage and Provide Startup Current to Vcc
9	CTRL	Programmable External Protection
10	FB	Feedback. Directly Connected to the Opto-Coupler
11	VCC	Supply Voltage of Driver and Control Circuits
12	DEM	Valley Detection for QR Control. Sample Vout to Realize SOVP and SUVP Protection
13	VCC_IN	Wide Range Input Supply Voltage to Produce Vcc
14	SENSE	Sense the Primary Current
15	GND	Signal Ground
16	S	The Source of Internal Power MOSFET



Functional Block Diagram





Absolute Maximum Ratings (Note 4)

Symbol	Parameter	Rating	Unit
Vhv	HV Pin Input Voltage	700	V
VD	Drain Pin Input Voltage	700	V
Vcc_in	LDO Supply Voltage	120	V
Vcc	Power Supply Voltage	34	V
lo	Gate Output Current	350	mA
Vfb, Vsense, Vctrl, Vdem	FB, VSENSE, VCTRL, VDEM Input Voltage to FB, SENSE, CTRL, DEM		V
ALθ	Thermal Resistance (Junction to Ambient) (Note 5)	77	°C/W
P _D	Power Dissipation at T _A < +25°C	500	mW
TJ	Operating Junction Temperature	-40 to +150	°C
Tstg	TsTG Storage Temperature Range		°C
ESD	Human Body Model (Except HV Pin and VCC_IN Pin) (Note 6)	3,000	V
E3D	Charged Device Model	600	V

Notes: 4. Stresses greater than those listed under *Absolute Maximum Ratings* can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to *Absolute Maximum Ratings* for extended periods can affect device reliability.

- 5. Test condition: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch² cooling area.
- 6. HV devices are ESD sensitive (HBM: V_{HV} = 500V, V_{CC_IN} = 450V).

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
Vcc	Supply Voltage	10	28	V
T _A	Ambient Temperature	-40	+85	°C

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Electrical Characteristics (@T_A = -40°C to +85°C, V_{CC} = 18V, unless otherwise specified.)

Supply Voltage (VCC Pin) Ist	Symbol	Parameter	Condition	Min	Тур	Max	Unit
IST	·				- 71-	1	
Cocpality Copening Graphy Copening Graphy		T ,	_	_	1	15	μA
	Icc	Operating Supply Current	V _{FB} = 4V, C _L = 0nF (Note 8)	1.2	1.6	2.2	A
VM Voc Maintain — 7.3 — V VUX.DO Shutdown Voltage — 6.1 6.7 7.1 V VCC-OVP — 32 33 34 V VCC-OVP — 32 33 34 V PWM Section/Oscillator Section Maximum Clamp Frequency (Note 8) — 120 — kHz fosc_MIN Minimum Clamp Frequency (Note 8) — ±12 — % fosc_MIN Minimum Clamp Frequency (Note 8) — ±12 — % fosc_MIN Minimum Clamp Frequency (Note 8) — ±12 — % fosc_MIN Minimum Clamp Frequency (Note 8) — ±12 — % fosc_MIN Minimum Clamp Frequency (Note 8) — ±12 — % Current Current Limit Threshold Voltage — — — 1.25 — V — — 1.25 <td>ICC-FAULT</td> <td>Operating Current If Fault Occurs</td> <td colspan="2">V_{FB} = 4V, V_{SENSE} = 0V (Note 8) 0.25</td> <td>0.4</td> <td>0.55</td> <td>mA</td>	ICC-FAULT	Operating Current If Fault Occurs	V _{FB} = 4V, V _{SENSE} = 0V (Note 8) 0.25		0.4	0.55	mA
Volucion Shutdown Voltage —	Vst	Startup Voltage	_	14.3	15.8	16.3	V
Voc. OVP Voc. OVP — 32 33 34 V	Vм	V _{CC} Maintain	_	_	7.3	_	V
PWM Section/Oscillator Section Focamina Focamina	V _{UVLO}	Shutdown Voltage	_	6.1	6.7	7.1	V
fosc-MAX	Vcc-ovp	Vcc OVP	_	32	33	34	V
Tosc_MIN Minimum Clamp Frequency (Note 8) 20 24 28 KHz	PWM Section/0	Oscillator Section			•	•	•
fosc-MIN Minimum Clamp Frequency (Note 8) 20 24 28 kHz fosc-JITER Valley Blanking Time Dithering (Note 8) ±12 % ton-Her Frequency Dithering Period 4 ms Ton-Her Frequency Dithering Period 4 No Vin-Stepse Section (SENSE Pin) 1.25 V Vollage 1.25 V Vollage 7 Cycles tea	fosc-max	Maximum Clamp Frequency	(Note 8)	_	120	_	kHz
TOTHER Frequency Dithering Period — — — — — Ms	fosc-min		(Note 8)	20	24	28	kHz
Vernet Sense Section (SENSE Pin)	fosc-JITTER	Valley Blanking Time Dithering	(Note 8)	_	±12	_	%
Vernet Sense Section (SENSE Pin)		, , ,	_			_	ms
VSENSE-MAX Current Limit Threshold Voltage IDEM_SOURCE = 200µA 0.89 0.96 1.04 V VTH-FOCP FOCP Voltage −		, , ,	1		I.	l	l .
The ELAY-FOCP FOCP Debounce Time (Note 9) -			IDEM_SOURCE = 200µA	0.89	0.96	1.04	V
LEB Leading Edge Blanking Time — 150 250 350 ns VTH-SSCP SSCP Voltage — — 100 — mV tsoFr-St Soft-Start Time — — 100 — mV tbELAY-SENSE Sense Propagation Delay (Note 7) — — 100 — ns Feedback Input Section (FB Pin) KFB-SENSE The Ratio of Input Voltage to Current — — 4 — V/V RFB Input Impedance — — 20 30 40 kΩ IFB-SOURCE Source Current VFB = 0V 0.1 0.2 0.3 mA Gor QR Mode Frequency Modulation Slope Versus VFB (Note 7) — — 94 — kHz/V VBURST Threshold for Entering Burst Mode — VDEM — — V AkHz/V VBURST Threshold for Entering Burst Mode — — — — V V V <	V _{TH-FOCP}	FOCP Voltage	_		1.25	_	V
The Barry Leading Edge Blanking Time — 150 250 350 ns	tDELAY-FOCP	FOCP Debounce Time (Note 9)	_	_	7	_	Cycles
Table Soft-Start Time Soft-Start Time Sense Propagation Delay (Note 7) Sense Voltage (Note 8) Sense Voltage (Note 7) Sense Voltage (Note 8) Sense Voltage (Note 7)	tLEB	, ,	_	150	250	350	ns
The Elay-Sense Sense Propagation Delay (Note 7)	VTH-SSCP	SSCP Voltage	_	_	100	_	mV
Feedback Input Section (FB Pin)	tsoft-st	Soft-Start Time	_	3	4	8	ms
The Ratio of Input Voltage to Current Sense Voltage (Note 7)	tDELAY-SENSE	Sense Propagation Delay (Note 7)	_	_	100	_	ns
The Ratio of Input Voltage to Current Sense Voltage (Note 7)	Feedback Inpu	t Section (FB Pin)			l	l	l .
IFB-SOURCE Source Current VFB = 0V 0.1 0.2 0.3 mA		The Ratio of Input Voltage to Current	_	_	4	_	V/V
OR Mode Frequency Modulation Slope Versus VFB (Note 7) −	R _{FB}	Input Impedance	_	20	30	40	kΩ
Slope Versus VFB (Note 7) - 94 - KH2/V	IFB-SOURCE	Source Current	V _{FB} = 0V	0.1	0.2	0.3	mA
VBURST Threshold for Entering Burst Mode 0.75V <v<sub>DEM<1.45V — 0.8 — V tON-MAX Maximum on Time (Note 8) 16 18.5 21 μs tDELAY-OLP Delay of Over Load Protection (Note 7) — — 70 — ms VFB-OLP Over Load Protection (Note 7) — — 4.2 — V Demagnetization Section (DEM Pin) VTH-DEM De-Magnetization Voltage (Note 7) — — 50 — mV VCLP-L Low Level for Clamping Voltage IDEM = 200μA (Source Current) -50 -5 — mV VTH-SOVP-L SOVP Threshold Voltage for Startup — 1.0 1.1 1.2 V VTH-SOVP-H SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V</v<sub>	GQR	• •	_	_	94	_	kHz/V
VDEM>1.45V — 0.933 — V ton-MAX Maximum on Time (Note 8) 16 18.5 21 μs tDELAY-OLP Delay of Over Load Protection (Note 7) — — 70 — ms VFB-OLP Over Load Protection (Note 7) — — 4.2 — V Demagnetization Section (DEM Pin) VTH-DEM De-Magnetization Voltage (Note 7) — 50 — mV VCLP-L Low Level for Clamping Voltage IDEM = 200μA (Source Current) -50 -5 — mV VCLP-H High Level for Clamping Voltage IDEM = -1mA (Sink Current) — 6 — V VTH-SOVP-H SOVP Threshold Voltage for Startup — 2.5 2.6 2.7 V			V _{DEM} <0.75V	_	0.66	_	V
ton-MAX Maximum on Time (Note 8) 16 18.5 21 μs tDELAY-OLP Delay of Over Load Protection (Note 7) — — 70 — ms VFB-OLP Over Load Protection (Note 7) — — 4.2 — V Demagnetization Section (DEM Pin) VTH-DEM De-Magnetization Voltage (Note 7) — — 50 — mV VCLP-L Low Level for Clamping Voltage IDEM = 200μA (Source Current) -50 -5 — mV VCLP-H High Level for Clamping Voltage IDEM = -1mA (Sink Current) — 6 — V VTH-SOVP-L SOVP Threshold Voltage for Startup — 1.0 1.1 1.2 V VTH-SOVP-H SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V	V _{BURST}	Threshold for Entering Burst Mode	0.75V <v<sub>DEM<1.45V</v<sub>	_	0.8	_	V
tDELAY-OLP Delay of Over Load Protection (Note 7) — — 70 — ms VFB-OLP Over Load Protection (Note 7) — — 4.2 — V Demagnetization Section (DEM Pin) VTH-DEM De-Magnetization Voltage (Note 7) — — 50 — mV VCLP-L Low Level for Clamping Voltage IDEM = 200μA (Source Current) -50 -5 — mV VCLP-H High Level for Clamping Voltage IDEM = -1mA (Sink Current) — 6 — V VTH-SOVP-L SOVP Threshold Voltage for Startup — 1.0 1.1 1.2 V VTH-SOVP-H SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V			V _{DEM} >1.45V	_	0.933	_	V
VFB-OLP (Noté 7) — 70 — ms VFB-OLP Over Load Protection (Note 7) — 4.2 — V Demagnetization Section (DEM Pin) VTH-DEM De-Magnetization Voltage (Note 7) — 50 — mV VCLP-L Low Level for Clamping Voltage IDEM = 200μA (Source Current) -50 -5 — mV VCLP-H High Level for Clamping Voltage IDEM = -1mA (Sink Current) — 6 — V VTH-SOVP-L SOVP Threshold Voltage for Startup — 1.0 1.1 1.2 V VTH-SOVP-H SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V	ton-max	Maximum on Time	(Note 8)	16	18.5	21	μs
Demagnetization Section (DEM Pin) VTH-DEM De-Magnetization Voltage (Note 7) — — 50 — mV VCLP-L Low Level for Clamping Voltage IDEM = 200μA (Source Current) -50 -5 — mV VCLP-H High Level for Clamping Voltage IDEM = -1mA (Sink Current) — 6 — V VTH-SOVP-L SOVP Threshold Voltage for Startup — 1.0 1.1 1.2 V VTH-SOVP-H SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V	tDELAY-OLP		_	_	70	_	ms
VTH-DEM De-Magnetization Voltage (Note 7) — 50 — mV VCLP-L Low Level for Clamping Voltage IDEM = 200μA (Source Current) -50 -5 — mV VCLP-H High Level for Clamping Voltage IDEM = -1mA (Sink Current) — 6 — V VTH-SOVP-L SOVP Threshold Voltage for Startup — 1.0 1.1 1.2 V VTH-SOVP-H SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V	Vfb-olp	Over Load Protection (Note 7)	_	_	4.2	_	V
VCLP-L Low Level for Clamping Voltage IDEM = 200μA (Source Current) -50 -5 — mV VCLP-H High Level for Clamping Voltage IDEM = -1mA (Sink Current) — 6 — V VTH-SOVP-L SOVP Threshold Voltage for Startup — 1.0 1.1 1.2 V VTH-SOVP-H SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V							
VCLP-L Low Level for Clamping Voltage IDEM = 200μA (Source Current) -50 -5 — mV VCLP-H High Level for Clamping Voltage IDEM = -1mA (Sink Current) — 6 — V VTH-SOVP-L SOVP Threshold Voltage for Startup — 1.0 1.1 1.2 V VTH-SOVP-H SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V	VTH-DEM	De-Magnetization Voltage (Note 7)	_	_	50	_	mV
VCLP-H High Level for Clamping Voltage IDEM = -1mA (Sink Current) — 6 — V VTH-SOVP-L SOVP Threshold Voltage for Startup — 1.0 1.1 1.2 V VTH-SOVP-H SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V	VCLP-L		IDEM = 200µA (Source Current)	-50	-5	_	mV
VTH-SOVP-L SOVP Threshold Voltage for Startup — 1.0 1.1 1.2 V VTH-SOVP-H SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V	V _{CLP-H}	, , ,	, , , , , , , , , , , , , , , , , , , ,	_		_	
V _{TH-SOVP-H} SOVP Threshold Voltage for Steady State — 2.5 2.6 2.7 V				1.0	1.1	1.2	V
		SOVP Threshold Voltage for Steady	_				
	tdeb-sovp	SOVP Debounce Time	_	_	7	_	Cycle

Notes: 7. Guaranteed by design.

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S. Data measured in IC test mode.
 Cycle-by-Cycle limit delay time contains OCP comparator delay time and driver delay time, Guaranteed by design.



Electrical Characteristics (continued) (@TA = -40°C to +85°C, Vcc = 18V, unless otherwise specified.)

Symbol	Parameter	Condition	Min	Тур	Max	Unit
Demagnetization Se	ection (DEM Pin)					
V _{TH-SUVP-L}	SUVP Threshold Voltage for Hiccup	_	_	0.5	_	V
tdeb-suvp	SUVP Debounce Time	_	_	7	_	Cycle
tBLANK-SUVP	SUVP Blank Time after Startup	_	15	20	25	ms
tsample	Sample Delay Time (Note 7)	_	_	2	_	μs
LDO Section (VCC	_IN Pin/VCC Pin)				T	
Vcc	LDO Regulated Voltage	Vcc Open, Vcc_in = 10V	9.0	9.8	10	V
	(Power Supply Voltage)	Vcc Open, Vcc_in = 40V	14	15	16	V
ILDO	Operating Current	Vcc=12V, Vcc_in = 40V	6	8	11	mA
Protection Section	,	T				
ICTRL-SOURCE	Source Current	<u> </u>	-110	-100	-90	μA
V _{TH-CTRL-L}	Low Threshold	_	0.97	1	1.03	V
tctrl-blank	Blank Time when VCTRL is Low	_	_	20	_	ms
V _{TH-CTRL-H}	High Threshold Voltage	_	2.9	3	3.1	V
VCTRL-CLP	Clamp Voltage (Note 11)	I _{CTRL} = -2mA		4.5	_	V
t _{DELAY-HICC}	Delay of Hiccup Protection (Note 7)	SUVP, SOVP, Line OVP, VCC OVP, FOCP, SSCP, CTRL Pin Protection	_	7	_	Cycles
HV Section (HV Pin)					
ICHARGE-L		Vcc = 0V, V _{HV} = 100V	_	0.23	_	mA
ICHARGE-H	Charge Current	Vcc = 6V, V _{HV} = 100V	_	2	_	mA
ICHARGE-FAULT	Charge Current if Fault Occurs	Vcc = 6V, V _{HV} = 100V	_	65	_	μΑ
V _{BR} -IN	Brown In Voltage	_	100	105	110	V
VBR-OUT	Brown Out Voltage	_	92	97	102	V
t _{BR-IN}	Delay of Brown In (Note 7)	_	_	100	_	μs
t _{BR-OUT}	Delay of Brown Out (Note 7)	_	_	50	_	ms
V_{LOVP}	Line OVP (Note 7)	_	_	630	_	V
V _H V	HV Pin Input Voltage (Note 10)	_	_	_	700	V
Internal OTP Sectio	• • • • • • • • • • • • • • • • • • • •					
OTP	OTP Threshold (Note 7)	_	_	+150	_	°C
Thys	OTP Recovery Hysteresis (Note 7)	_	<u> </u>	+125	_	°C
tDEB-OTP	OTP Debounce Time	_	_	7	_	Cycle
Power MOSFET Sec		•	•		•	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	_	700	_	_	V
R _{DS(ON)}	Drain-Source On State Resistance	<u> </u>	_	1.26	2	Ω

Notes:

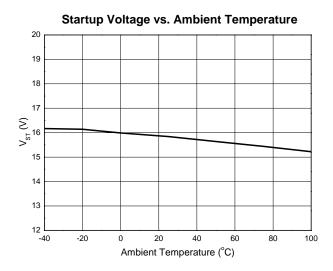
^{7.} Guaranteed by design.
8. Data measured in IC test mode.
9. Cycle-by-Cycle limit delay time contains OCP comparator delay time and driver delay time, Guaranteed by design.

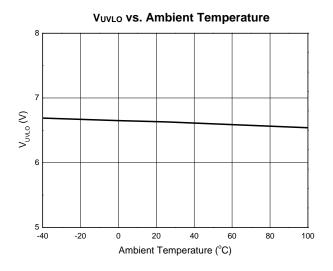
^{10.} The drain-source voltage is 80% of VDS in the aging condition.

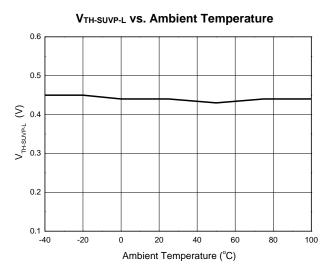
^{11.} The sourcing current of CTRL pin must be limited below 5mA. Otherwise it may cause permanent damage to the device.

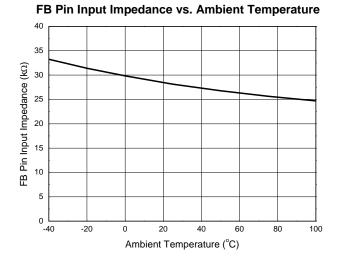


Performance Characteristics



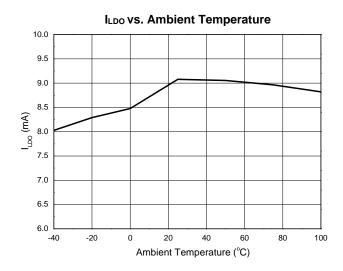


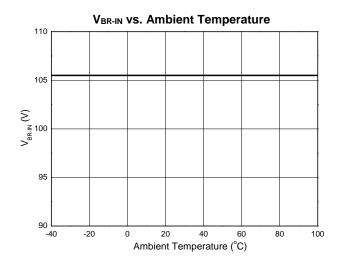




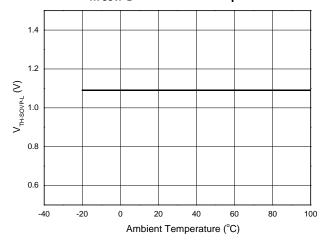


Performance Characteristics (continued)





V_{TH-SOVP-L} vs. Ambient Temperature





Operation Description

Quasi-Resonant (QR) Mode

Quasi-Resonant operation is regarded as a soft switching technology which always turns on the primary MOSFET at the valley status of Drain-to-Source voltage (Vps). Compared to traditional hard switching, QR switching-on can reduce the switching power loss of MOSFET and achieve good EMI behavior without any additional BOM cost.

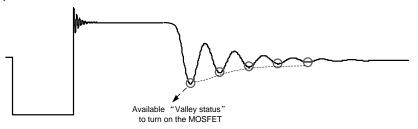


Figure 1

Figure 1 shows the primary MOSFET VDS waveform. When the secondary-side current flows to zero, the primary inductance LM and the effective MOSFET output capacitor Coss would be resonant. The valley is detected by DEM pin through a pair of voltage divider. At primary MOSFET turning off time, once the voltage on DEM pin is detected below 50mV, one "valley status" is counted. To prevent the false trigger of the VDs ring caused by leakage inductance, the valley detection function is blanked within the tsample (2µs, refer to Figure 6) when primary MOSFET turns off.

Each "valley status" of MOSFET Vps will be detected and counted by DEM pin. According to the frequency control strategy of AP39303, one proper "valley status" will be selected to turn on the MOSFET.

Frequency Modulation Strategy

The AP39303 operates with QR mode, green mode and burst mode to achieve the high efficiency performance.

In general, the AP39303 power system operates with first "valley status" under low line and full load condition, in which the maximum primary peak current and transformer flux density occur. The power system designer is required to choose transformer size and switching frequency according to this worst case condition.

With output load decreasing from full load in the first "valley status", the switching frequency of AP39303 increases correspondingly. In order to avoid performance degrading at very high switching frequency operation, there is a fixed 120kHz maximum frequency limitation in AP39303. Since too high switching frequency will lead to the worse performance, the 120kHz frequency limitation is not preferred to reach in system design. Actually AP39303 has built-in reference in FB pin voltage to adjust "valley status" for green mode operation, as shown in Figure 2. When FB pin voltage decreases to a modulating reference, the first "valley status" is forced to shift to other available "valley status".

The AP39303 has the minimum switching frequency limit of 24kHz to avoid audible noise issue. When the switching frequency decrease to 24kHz with output load decreasing, the switching frequency will keep at 24kHz. When FB pin voltage is lower than VBURST, the power system enters burst mode to reduce the power dissipation under very light load condition.



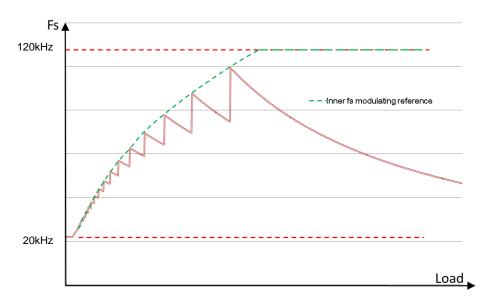


Figure 2

Active Frequency Dithering

To improve the EMI performance, the AP39303 integrates an active frequency dithering function. A consecutive frequency-dithering signal is injected to the SENSE pin after Leading-Edge Blanking (LEB) time. As shown in Figure 3, the frequency-dithering signal is repeating over and over again with a period of 4ms and amplitude of +/-Vs_JITTER. With the injection of frequency-dithering signal on SENSE pin, the switching frequency will have a periodical excursion to improve the EMI performance.

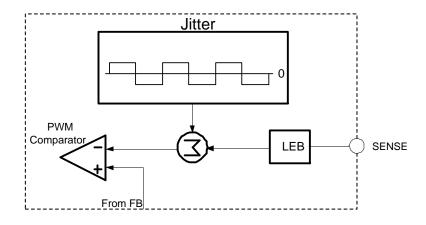


Figure 3

Current Mode PWM Control

The AP39303 operates as a current mode controller; the output switch is turned on by every oscillator cycle and turned off when the primary peak current reaches the threshold level established by the FB pin. The primary current signal is converted to a voltage signal on current sense resistor Rs. The relation between primary peak current (I_{PK}) and V_{FB} is:

$$I_{PK} = V_{FB} / 4R_S$$

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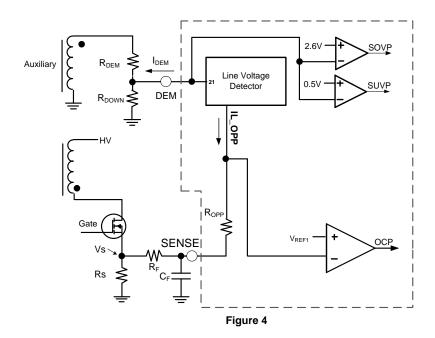
Constant Over Current Protection

Cycle-by-cycle current limit is a popular method to achieve output over current protection. Actually, the turn-off delay of the MOSFET and the higher switching frequency always result in the higher OCP current at high line voltage. To obtain a constant OCP current value with universal input voltage, AP39303 adopts an effective line compensation circuitry. The function block is illustrated in Figure 4. The current IDEM which reflects line voltage is scaled down and inversed to IL_OPP within AP39303, this IL_OPP flows through the inner compensation resistor ROPP and an external filtering resistor RF, and then the final line compensation voltage is formed as:

$$V_S + \frac{Vindc * Naux}{Np * Rdem * 21} * (R_{OPP} + R_F) = V_{REF1}$$

Where V_{S} is the sense voltage of R_{S}

As above formula indicates, changing the compensation voltage at different line voltage is a good way to balance the OCP current. In a real system, usually keep the R_{DEM} value fixed (220k Ω is recommended). To change the line compensation voltage, a good solution is to change R_F . Whenever the R_F is changed, adjust the C_F at the same time to offer an enough RC time to filter the spike on SENSE pin.



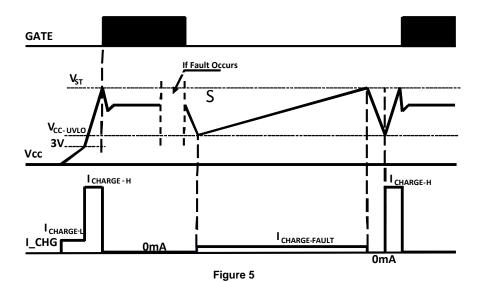
HV Start-Up Circuit

A built-in HV startup circuit in AP39303 can help to simplify the power system design for ultra-low standby application. For AP39303, there are two HV Start-Up charging current: the $I_{CHARGE-L}$ when V_{CC} is lower than 3V and the $I_{CHARGE-H}$ when the V_{CC} voltage rises above 3V, which can prevent the IC from overheat when V_{CC} short-to-GND fault happens. The HV startup circuit will stop working and have no additional power dissipation when V_{CC} voltage reaches the V_{ST} , then the AP39303 starts working and will supply energy to V_{CC} from auxiliary winding.

However, the charging process described above is only for the normal system startup condition. Once some system faults occur and the protection process is triggered, AP39303 will shut down and Vcc voltage will begin to decrease. The HV startup circuit starts working again when Vcc voltage decreases below Vcc-uvLo, and charges the Vcc capacitor with current of Icharge-Fault. This special design can reduce the input power dissipation when system fault happens, especially for output short condition. The HV Start-Up circuit working process is illustrated in Figure 5.

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Built-In Vcc LDO

The AP39303 integrates a V_{CC} LDO circuitry, the LDO regulates the wide range V_{CC_IN} which is rectified from auxiliary winding to an acceptable value. It makes the AP39303 a good choice in wide range output voltage application.

Brown In/Out Protection

To avoid potential high-current stress at low line voltage, the AP39303 introduces a reliable brownout protection. The AC line voltage is detected through HV pin, a pair of high-voltage diodes are connected to the AC line which will rectify the AC input voltage to a double-frequency positive voltage referring to GND, a $20k\Omega$ resistor is recommended to be added to improve the surge immunity. When the voltage across HV pin is higher than V_{BR-IN} for about 100μ s of t_{BR-IN} and V_{CC} reaches V_{ST} , the system starts to work. If the HV pin voltage falls below V_{BR-OUT} and lasts for 50ms of t_{BR-OUT} , the system will shut down until the line voltage rises over its brown-in voltage again.

SOVP/SUVP Protection

The AP39303 provides output OVP and UVP protection function. The auxiliary winding voltage during secondary rectifier conducting period reflects the output voltage. A voltage divide network is connected to the auxiliary winding and DEM pin, the DEM pin will detect the equivalent output voltage with a delay of tsample from the falling edge of GATE driver signal, as shown in Figure 6. The detected voltage will be compared to the SOVP and SUVP threshold voltage Vth-sovP and Vth-suvP. If the SOVP or SUVP threshold is reached continuously by 7 switching cycles, the SOVP or SUVP protection will be triggered, the AP39303 will shut down and the system will restart when the Vcc voltage falls below the UVLO voltage.

To prevent from false-trigger of SUVP during start up process, a blank time of tBLANK-SUVP is set during which the SUVP protection function is ignored.

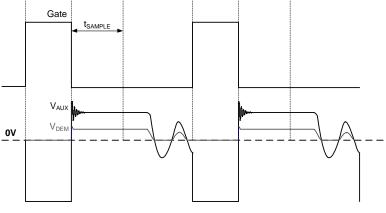


Figure 6



Externally Triggered Protection

The AP39303 reserves flexible protection mode for power design. The CTRL pin can achieve external programmable protection. A high threshold of $V_{TH-CTRL-H}$ is set for any over voltage protection, if the CTRL pin voltage is higher than the threshold for 7 switching cycles, the CTRL-High protection will be triggered. A low threshold of $V_{TH-CTRL-L}$ is usually used for external over temperature protection. To realize the external OTP, a proper NTC should be connected from the CTRL pin to the ground. An inner current of 100 μ A flows through the NTC from the CTRL pin. If the CTRL pin voltage is lower than the $V_{TH-CTRL-L}$ for 32ms duration at least, the CTRL-Low protection will be triggered. Whenever the protection is triggered, the system will stop the output drive signal and will restart after the V_{CC} voltage falling below the UVLO voltage.

System Protection

LOVP, FOCP, SSCP, VCC OVP, OTP

The AP39303 provides versatile protection to ensure the reliability of the power system. LOVP achieves line voltage overvoltage protection, if the detected AC line voltage is higher than VLOVP for 7 switching cycles, the LOVP protection will be triggered. FOCP protection is an ultra-fast short-current protection which is helpful to avoid catastrophic damage of the system when the secondary rectifier is short. The primary peak current will be monitored by SENSE pin through a primary sense resistor, whenever the sampled voltage reaches the threshold of VTH-FOCP for 7 switching cycles continuously, the FOCP protection will be activated to shut down the switching pulse. SSCP might be triggered at ultra-low DC bus voltage condition or other failure condition that short the SENSE pin to ground. The SSCP module senses the voltage across the primary sense resistor with a delay of 3µs after the rising edge of primary GATE signal, this sensed signal is compared with VTH-SSCP. If it is lower than VTH-SSCP for 7 switching cycles, the SSCP protection will be triggered and the drive signal will be disabled. All these protections described above will restart the system when the Vcc voltage falls below UVLO. Although the external OTP can be easily implemented through CTRL pin, the AP39303 still reserves the inner OTP with a hysteresis for any necessary use.

Vcc Maintain Mode

During light-load or transient-load condition, VFB will drop and be lower than VBURST, thus the PWM drive signal will be stopped, and there is no energy for transferring to the output. Therefore, the IC VCC supply voltage may decrease to the UVLO threshold voltage and system may enter the unexpected restart mode. To avoid this, the AP39303 holds a so-called VCC maintain mode which can supply energy to VCC.

When Vcc decreases to a setting threshold as VM, the Vcc maintain mode will be awaked and a charging current of Icharge-H will flow to the Vcc pin. With Vcc maintain mode, the Vcc is not easy to touch the shutdown threshold during the startup process and transient load condition. This will also simplify the system design. The minimum Vcc voltage is suggested to be designed a little higher than Vcc maintain threshold thus can achieve the best balance between the power loss and step load performance.

Leading-Edge Blanking Time

A narrow spike on the leading edge of the current waveform can usually be observed when the power MOSFET is turned on. A 250ns leading-edge blank is built-in to prevent the false-trigger caused by the turn-on spike. During this period, the current limit comparator and the PWM comparator are disabled and the gate driver cannot be switched off.

At the time of turning-off the MOSFET, a negative undershoot (maybe larger than -0.3V) can occur on the SENSE pin. So it is strongly recommended to add a small RC filter or at least connect a resistor "R" on this pin to protect the IC (Shown as Figure 7).

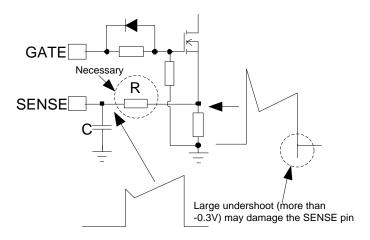


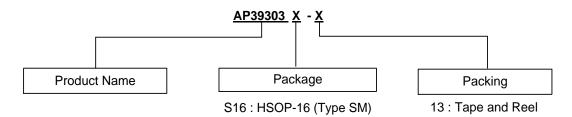
Figure 7

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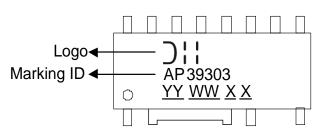
Ordering Information



5 (1)			13"Tape and Reel		
Part Number	Package	Marking ID	Quantity	Part Number Suffix	
AP39303S16-13	HSOP-16 (Type SM)	AP39303	4000/Tape and Reel	-13	

Marking Information

(Top View)



YY: Year: 18,19, 20~ WW: Week: 01~52; 52 represents 52 and 53 week

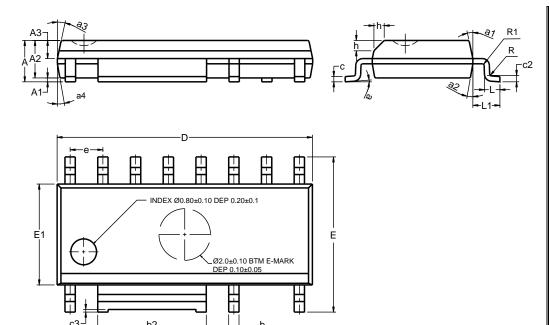
XX: Internal Code



Package Outline Dimensions (All dimensions in mm)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: HSOP-16 (Type SM)



HSOP-16 (Type SM)					
Dim	Min	Max	Тур		
Α	1.35	1.75	1.60		
A1	0.10	0.25	0.15		
A2	1.25	1.65	1.45		
A3	0.55	0.75	0.65		
b	0.36	0.51			
b2	4.17	4.32			
С	0.17	0.25			
c2	0.25BSC				
с3	0.00	0.15			
D	9.80	10.00	9.90		
Е	5.80	6.20	6.00		
E1	3.80	4.00	3.90		
е		1.27BS0	\sim		
h	0.30	0.50	0.40		
L	0.45	0.80	0.60		
L1		1.04RE	=		
R	0.07				
R1	0.07				
а	0°	8°			
a1	10°	14°	12°		
a2	8°	12°	10°		
a3	10°	14°	12°		
a4	8°	12°	10°		
All Dimensions in mm					

Mechanical Data

- Moisture Sensitivity: MSL Level 3 per JESD22-A113
- Terminals: Finish Matte Tin Plated Leads, Solderable per JESD22-B102 (3)
- Weight: 0.168 grams (Approximate)

November 2020

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